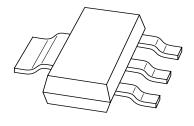
DISCRETE SEMICONDUCTORS

DATA SHEET



BF720; **BF722** NPN high-voltage transistors

Product data sheet Supersedes data of 1996 Dec 05 1999 Apr 21



NPN high-voltage transistors

BF720; BF722

FEATURES

• Low feedback capacitance.

APPLICATIONS

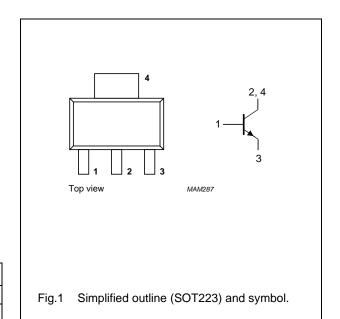
- Class-B video output stages of colour television receivers
- General purpose high voltage circuits.

DESCRIPTION

NPN transistors in a SOT223 plastic package. PNP complement: BF723.

PINNING

PIN	DESCRIPTION	
1	base	
2, 4	collector	
3	emitter	



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BF720		_	300	V
	BF722		_	250	V
V _{CEO}	collector-emitter voltage	open base			
	BF720		_	300	V
	BF722		_	250	V
V _{EBO}	emitter-base voltage	open collector	-	5	V
I _C	collector current (DC)		_	100	mA
I _{CM}	peak collector current		_	200	mA
I _{BM}	peak base current		_	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	1.2	W
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

 Device mounted on printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see "Thermal considerations for SOT223 in the General Part of associated Handbook".

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NPN high-voltage transistors

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	106	K/W
R _{th j-s} thermal resistance from junction to soldering point		note 1	25	K/W

Note

1. Device mounted on printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see "Thermal considerations for SOT223 in the General Part of associated Handbook".

CHARACTERISTICS

 $T_j = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 200 V	_	10	nA
		I _E = 0; V _{CB} = 200 V; T _j = 150 °C	_	10	μΑ
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = 5 V	_	50	nA
h _{FE}	DC current gain	I _C = 25 mA; V _{CE} = 20 V	50	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 30 \text{ mA}; I_B = 5 \text{ mA}$	_	0.6	V
C _{re}	feedback capacitance	I _C = i _c = 0; V _{CE} = 30 V; f = 1 MHz	_	1.6	pF
f _T	transition frequency	I _C = 10 mA; V _{CE} = 10 V; f = 100 MHz	60	_	MHz

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NPN high-voltage transistors

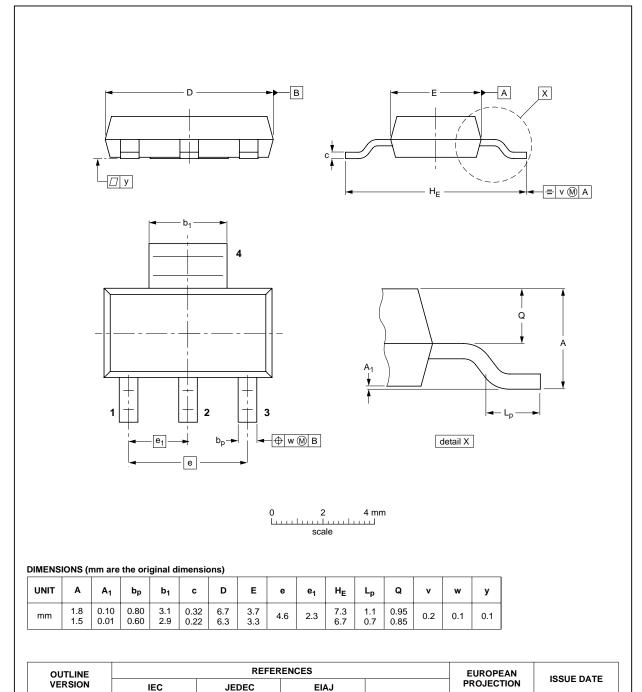
BF720; BF722

97-02-28 99-09-13

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



SC-73

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SOT223

NPN high-voltage transistors

BF720; BF722

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION	
Objective data sheet	Development	This document contains data from the objective specification for product development.	
Preliminary data sheet	Qualification	n This document contains data from the preliminary specification.	
Product data sheet	Production	This document contains the product specification.	

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- 1. Please consult the most recently issued document before initiating or completing a design.
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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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